



ELECTRONIC TUBE REFERENCE

QQV0325

Power - Tetrode (NOT beam) electronic tube

CONSOLIDATED TECHNICAL DATA

1 SECTION
CONSTRUCTION
TETRODE

UHF power double tetrode designed for VHF/UHF amplification and frequency multiplication to approximately 600 MHz. Two power sections provide compact high-frequency operation.

GENERAL CHARACTERISTICS

BASE DESIGNATION	—	BASE PINS	—
NOMINAL HEATER	6.3 V / 1.3 A	PARALLEL HEATER	6.3 V / 1.3 A
HEATING	Indirect	SERIES OPERATION	Capable
CATHODE ARRANGEMENT	Separate cathodes	SECTION CONSTRUCTION	Similar

SECTION RATINGS

SECTION1 Tetrode	
TRANSCONDUCTANCE	0.0025 S
MAXIMUM PLATE VOLTAGE	750 V
MAXIMUM SCREEN VOLTAGE	250 V
MAXIMUM PLATE DISSIPATION	12.5 W
Two electrically similar RF tetrode sections; represented once under identical-section compression.	

UHF power double tetrode for VHF/UHF amplifier and frequency-multiplier service to 600 MHz.

SOURCE OPERATING CONDITIONS

[SOURCE PDF](#)

1963 Mullard

Published test conditions and operating points. Values on this page are preserved as reported by this source.

1963 MULLARD

Section 1 · Tetrode

OTHER		
PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Maximum operating frequency	600 MHz	—
RF operating frequency	180 MHz	ClassC
RF plate voltage	700 V	ClassC
RF screen voltage	250 V	ClassC
RF control-grid voltage	-65 V	ClassC
RF plate current per section	60 mA	ClassC
RF output power	67 W	ClassC
RF operating frequency	470 MHz	ClassC
RF plate voltage	500 V	ClassC
RF screen voltage	250 V	ClassC
RF control-grid voltage	-55 V	ClassC
RF plate current per section	60 mA	ClassC
RF output power	38 W	ClassC
RF operating frequency	600 MHz	ClassC
RF plate voltage	400 V	ClassC
RF screen voltage	250 V	ClassC
RF control-grid voltage	-50 V	ClassC
RF plate current per section	59 mA	ClassC
RF output power	22 W	ClassC
RF operating frequency	475 MHz	ClassC,FrequencyMultiplier
RF plate voltage	300 V	ClassC,FrequencyMultiplier
RF screen voltage	250 V	ClassC,FrequencyMultiplier
RF control-grid voltage	-175 V	ClassC,FrequencyMultiplier

PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
RF plate current per section	50 mA	ClassC,FrequencyMultiplier
RF output power	10 W	ClassC,FrequencyMultiplier
Base-pin temperature maximum	180 C	—
Bulb/anode-seal temperature maximum	250 C	—

CAPACITANCE		
PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Plate-grid capacitance per section	0.04 pF	—
Push-pull input capacitance	4.4 pF	PushPull
Push-pull output capacitance	1.6 pF	PushPull
Grid-to-all capacitance per section	7.5 pF	—
Plate-to-all capacitance per section	2.6 pF	—

CHARACTERISTICS		
PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Transconductance	2.5 mA/V	—
Grid1-to-grid2 amplification factor	8	—

APPLICATION		
PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Application	RF power amplifier / oscillator / frequency multiplier	—